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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HSM2694

Silicon Epitaxial Planar Diode for Tuner Band Switch

RENESAS

ADE-208-095A (Z)

Rev. 1
Jun. 1993

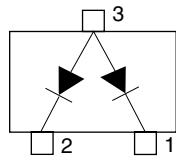
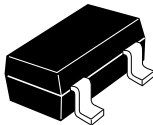
Features

- Low forward resistance. ($r_f = 0.9\Omega_{\max}$)
- Low capacitance. ($C = 1.2\text{pF}_{\max}$)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM2694	B3	MPAK

Pin Arrangement



(Top View)

- 1 Cathode
- 2 Cathode
- 3 Anode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Power dissipation	Pd^*	150	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-45 to +125	°C
Operation temperature	T_{opr}	-20 to +60	°C

Note: Two device total

Electrical Characteristics *

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	35	—	—	V	$I_R = 10\mu A$
Reverse current	I_R	—	—	50	nA	$V_R = 25V$
Forward voltage	V_F	—	—	1.0	V	$I_F = 10mA$
Capacitance	C	—	—	1.2	pF	$V_R = 6V, f = 1MHz$
Forward resistance	r_f	—	—	0.9	Ω	$I_F = 2mA, f = 100MHz$

Note: Per one device

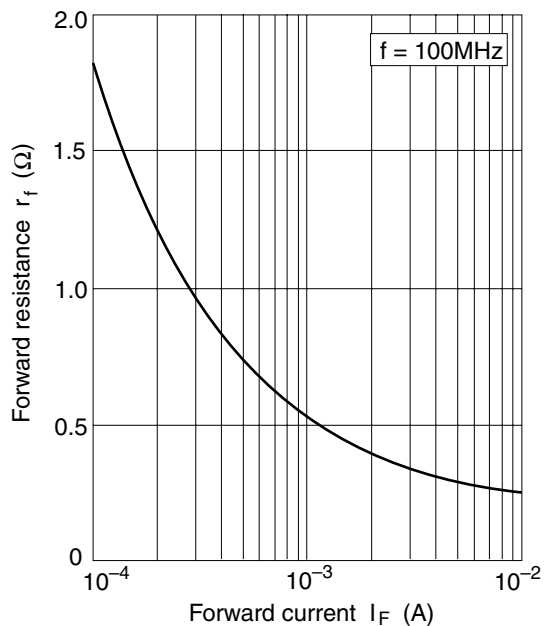


Fig.1 Forward resistance Vs. Forward current

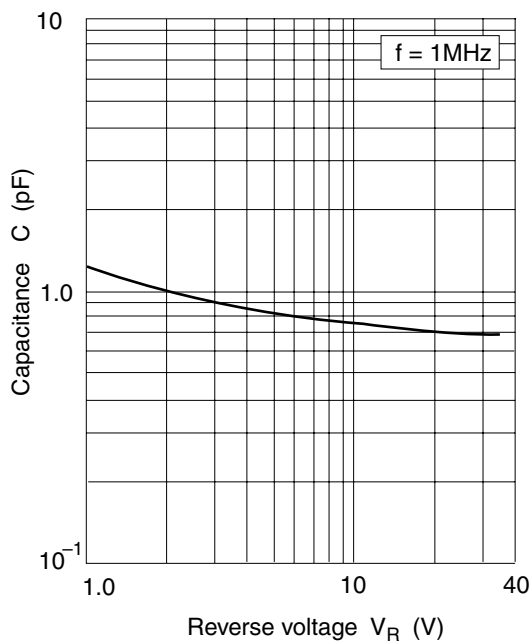


Fig.2 Capacitance Vs. Reverse voltage

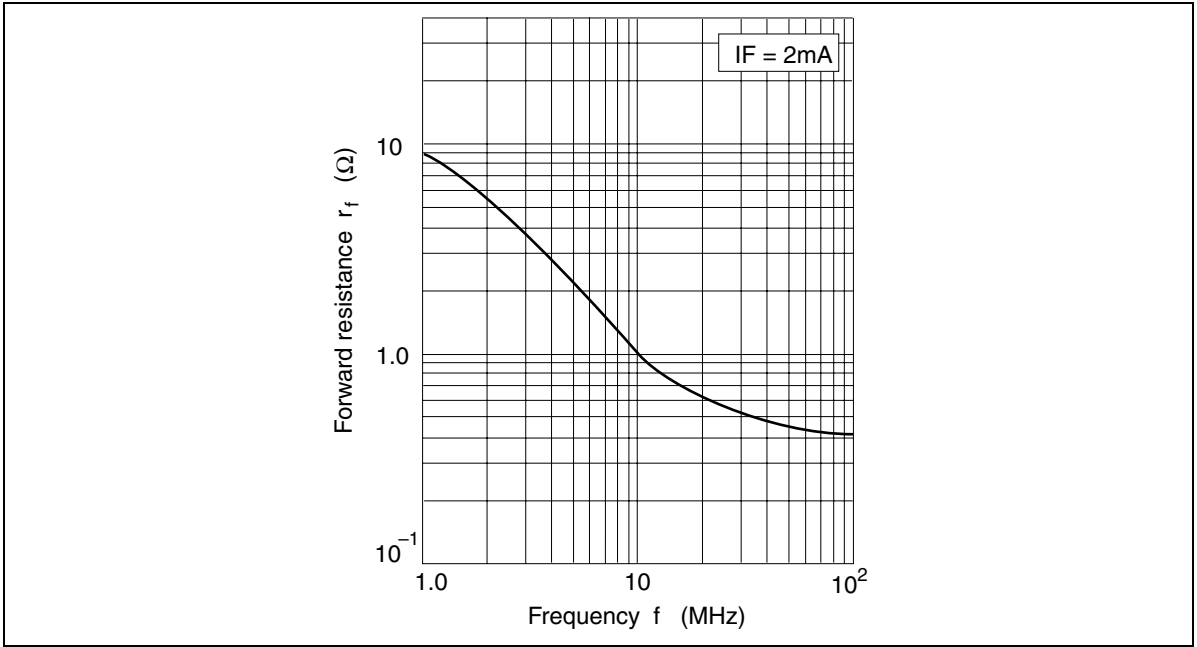
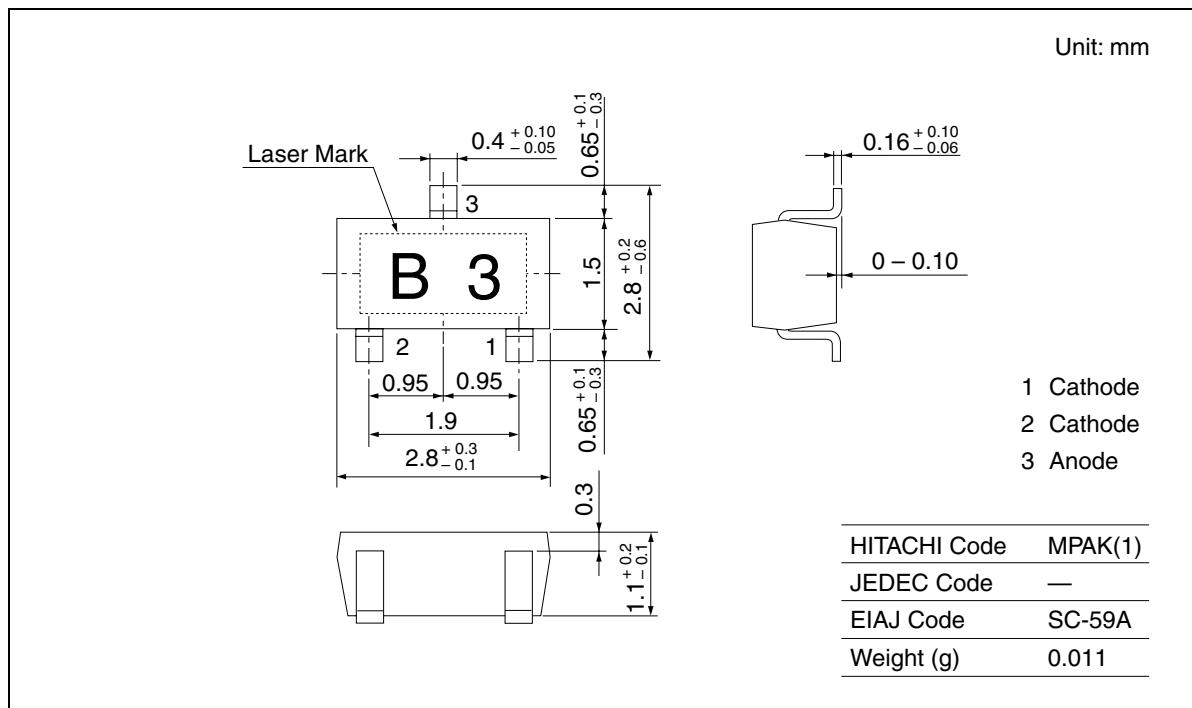


Fig.3 Forward resistance Vs. Frequency

Package Dimensions



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